MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK7Q65W

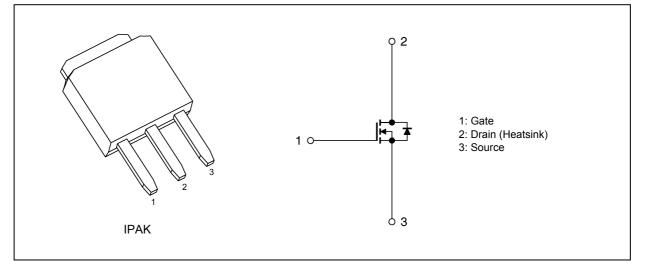
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.66 \Omega(typ.)$ by using Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: V_{th} = 2.5 to 3.5 V(V_{DS} = 10 V, I_D = 0.25 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	650	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	Ι _D	6.8	A
Drain current (pulsed)	(Note 1)	I _{DP}	27.2	
Power dissipation (T _c = 2	5 °C)	PD	60	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	90	mJ
Avalanche current		I _{AR}	1.7	A
Reverse drain current (DC)	(Note 1)	I _{DR}	6.8	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	27.2	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2014-09

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	2.09	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	125	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 55.3 mH, R_G = 25 Ω , I_{AR} = 1.7 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V			10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	650	_	—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.25 mA	2.5	_	3.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 3.4 A		0.66	0.8	Ω

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 1 MHz	_	490	_	pF
Reverse transfer capacitance	C _{rss}			1.7	_	
Output capacitance	C _{oss}		_	13	_	
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V	_	21	_	
Gate resistance	r _g	V _{DS} = OPEN , f = 1 MHz		7	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1		13	_	ns
Switching time (turn-on time)	t _{on}			35	_	
Switching time (fall time)	t _f]	_	4	_	
Switching time (turn-off time)	t _{off}]	_	52	_	1
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 3.4 A	50	_	_	V/ns

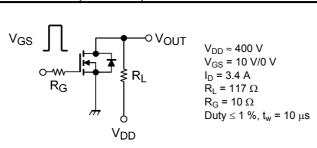


Fig. 6.2.1 Switching Time Test Circuit

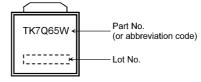
6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 6.8 \text{ A}$		15	—	nC
Gate-source charge 1	Q _{gs1}		_	3.2	_	
Gate-drain charge	Q _{gd}			7	_	

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

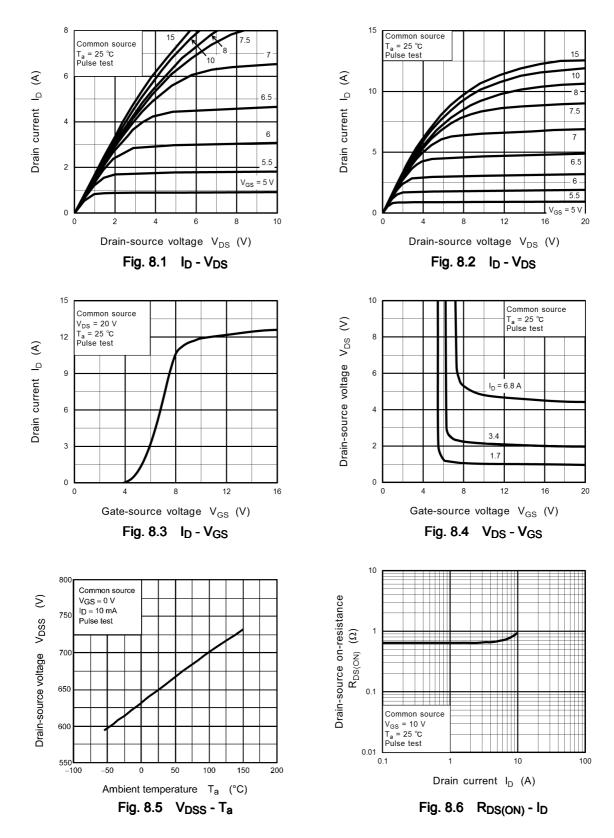
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 6.8 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 3.4 A, V _{GS} = 0 V	_	180	_	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 100 A/μs	_	1.7	_	μC
Peak reverse recovery current	I _{rr}		_	16	_	А
Diode dv/dt ruggedness	dv/dt	I _{DR} = 3.4 A, V _{GS} = 0 V, V _{DD} = 400 V	15			V/ns

7. Marking





8. Characteristics Curves (Note)



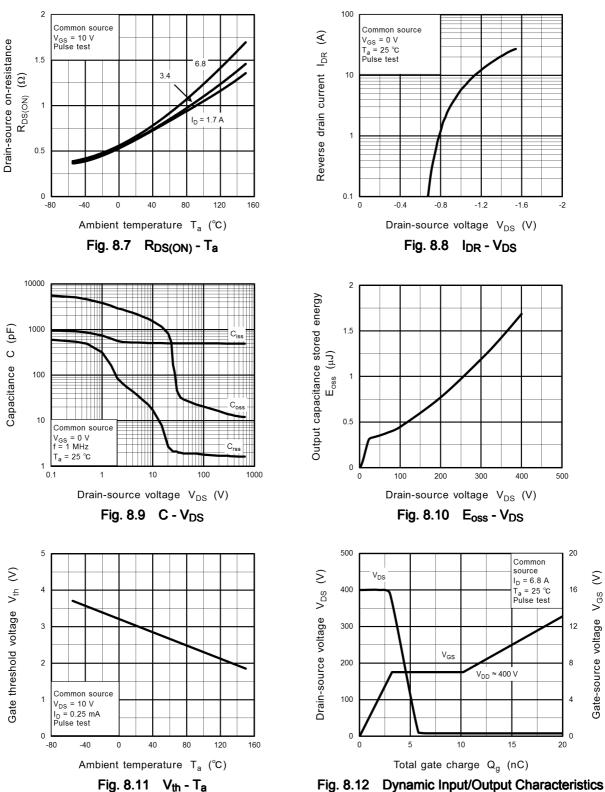


Fig. 8.12 Dynamic Input/Output Characteristics

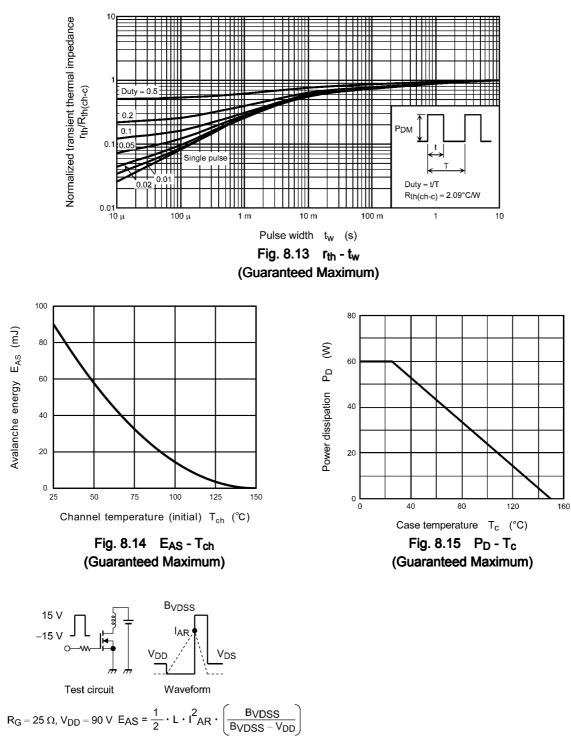
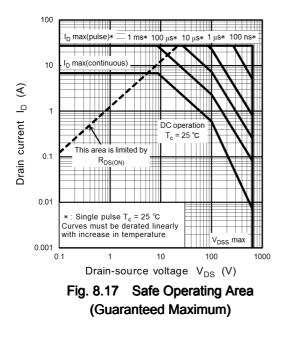


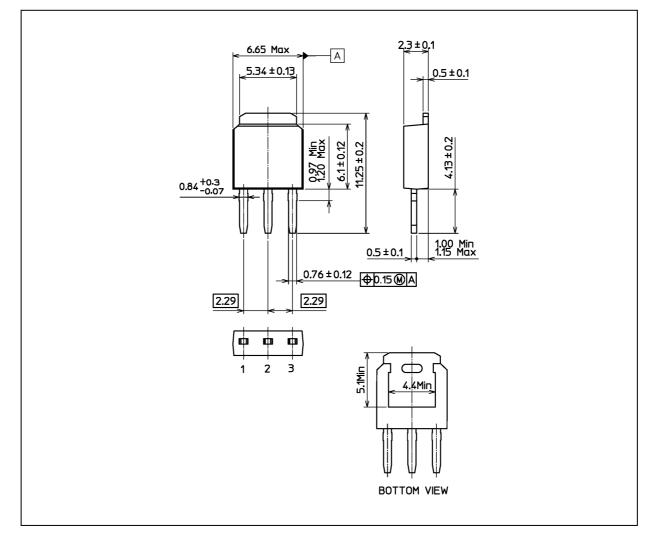
Fig. 8.16 Test Circuit/Waveform



Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.337 g (typ.)

	Package Name(s)
TOSHIBA: 2-7L1A	
Nickname: IPAK	

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